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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 14x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl25z128vlh4

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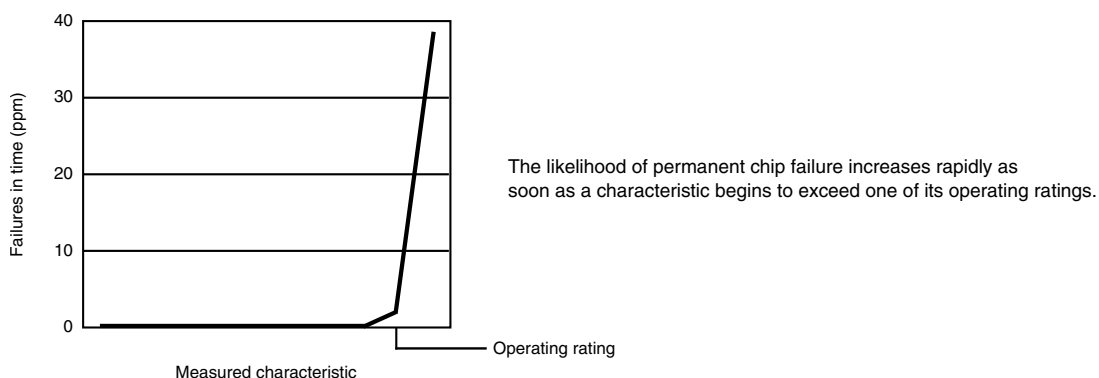
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3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



3.6 Relationship between ratings and operating requirements

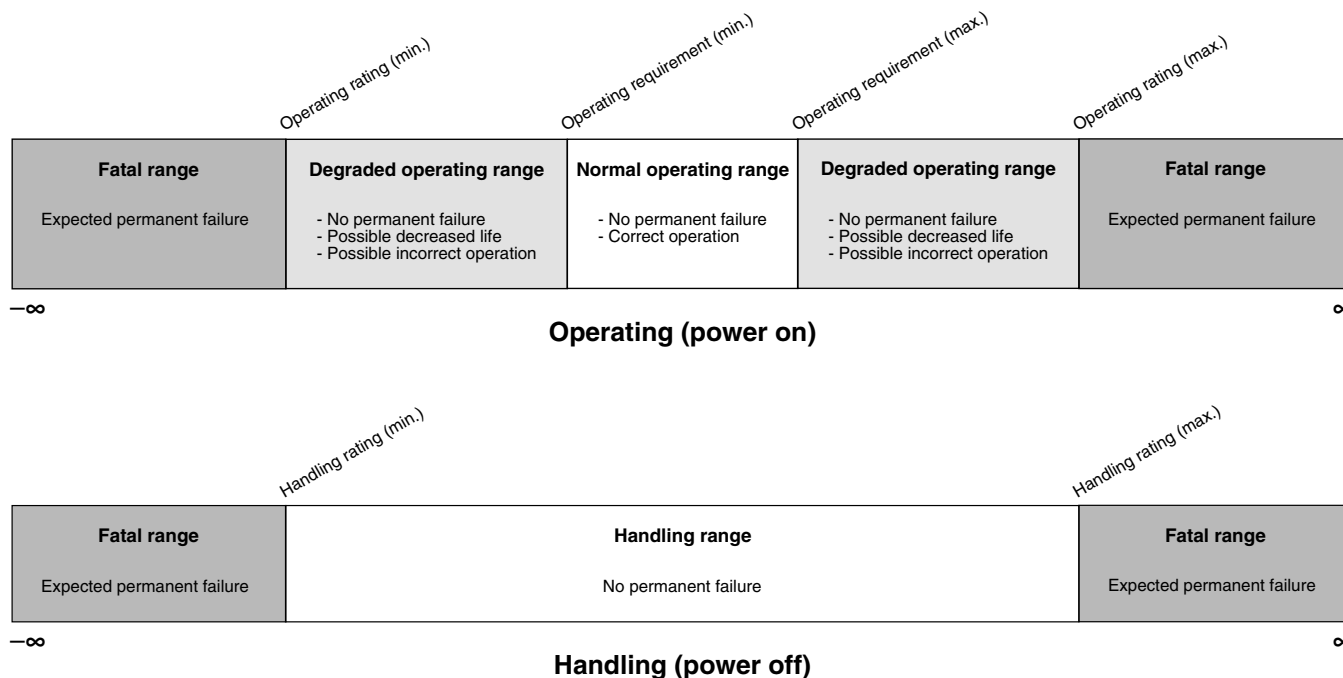


Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
V _{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I _{CDIO}	Digital pin negative DC injection current — single pin • $V_{IN} < V_{SS}-0.3V$	-5	—	mA	1
I _{CAIO}	Analog ² pin DC injection current — single pin • $V_{IN} < V_{SS}-0.3V$ (Negative current injection) • $V_{IN} > V_{DD}+0.3V$ (Positive current injection)	-5 —	— +5	mA	3
I _{Ccont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	-25 —	— +25	mA	
V _{RAM}	V _{DD} voltage required to retain RAM	1.2	—	V	

1. All digital I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{DIO_MIN} (=V_{SS}-0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO_MIN}-V_{IN})/|I_{IC}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} (=V_{SS}-0.3V) and V_{IN} is less than V_{AIO_MAX}(=V_{DD}+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V _{LVW1H}	Low-voltage warning thresholds — high range • Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	1
V _{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V _{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V _{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	

Table continues on the next page...

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{LVW1L}	Low-voltage warning thresholds — low range					1
	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V _{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -5 mA	V _{DD} - 0.5	—	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -1.5 mA	V _{DD} - 0.5	—	V	
V _{OH}	Output high voltage — High drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -18 mA	V _{DD} - 0.5	—	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -6 mA	V _{DD} - 0.5	—	V	
I _{OHT}	Output high current total for all ports	—	100	mA	
V _{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OL} = 1.5 mA	—	0.5	V	
V _{OL}	Output low voltage — High drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OL} = 18 mA	—	0.5	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OL} = 6 mA	—	0.5	V	
I _{OLT}	Output low current total for all ports	—	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	2
I _{IN}	Input leakage current (per pin) at 25 °C	—	0.025	μA	2
I _{IN}	Input leakage current (total all pins) for full temperature range	—	65	μA	2
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	

Table continues on the next page...

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V	—	300	745	μA	5, 4
I _{DD_VLPW}	Very low power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	135	496	μA	5
I _{DD_STOP}	Stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	345 357 392 438 551	490 827 869 927 1065	μA	
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	4.4 10 20 37 81	16 35 50 112 201	μA	
I _{DD_LLS}	Low leakage stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	1.9 3.6 6.5 13 30	3.7 39 43 49 69	μA	
I _{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	1.4 2.5 5.1 9.2 21	3.2 19 21 26 38	μA	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0V at 25°C at 50°C at 70°C at 85°C at 105°C	— — — — —	0.7 1.3 2.3 5.1 13	1.4 13 14 17 25	μA	

Table continues on the next page...

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{ADC}	ADC peripheral adder combining the measured values at VDD and VDDA by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μA

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

5.4.2 Thermal attributes

Table 10. Thermal attributes

Board type	Symbol	Description	80 LQFP	64 LQFP	48 QFN	32 QFN	Unit	Notes
Single-layer (1S)	R _{θJA}	Thermal resistance, junction to ambient (natural convection)	70	71	84	92	°C/W	1
Four-layer (2s2p)	R _{θJA}	Thermal resistance, junction to ambient (natural convection)	53	52	28	33	°C/W	
Single-layer (1S)	R _{θJMA}	Thermal resistance, junction to ambient (200 ft./min. air speed)	—	59	69	75	°C/W	
Four-layer (2s2p)	R _{θJMA}	Thermal resistance, junction to ambient (200 ft./min. air speed)	—	46	22	27	°C/W	
—	R _{θJB}	Thermal resistance, junction to board	34	34	10	12	°C/W	2
—	R _{θJC}	Thermal resistance, junction to case	15	20	2.0	1.8	°C/W	3
—	Ψ _{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	0.6	5	5.0	8	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions — Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions — Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions — Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions — Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 SWD Electricals

Table 11. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V

Table continues on the next page...

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.3.1 MCG specifications

Table 12. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{\text{ints_ft}}$	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C	—	32.768	—	kHz	
$f_{\text{ints_t}}$	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta f_{\text{dco_res_t}}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{\text{dco}}$	1
$\Delta f_{\text{dco_t}}$	Total deviation of trimmed average DCO output frequency over voltage and temperature	—	+0.5/-0.7	± 3	$\%f_{\text{dco}}$	1, 2
$\Delta f_{\text{dco_t}}$	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0 - 70 °C	—	± 0.4	± 1.5	$\%f_{\text{dco}}$	1, 2
$f_{\text{intf_ft}}$	Internal reference frequency (fast clock) — factory trimmed at nominal V_{DD} and 25 °C	—	4	—	MHz	
$\Delta f_{\text{intf_ft}}$	Frequency deviation of internal reference clock (fast clock) over temperature and voltage --- factory trimmed at nominal V_{DD} and 25 °C	—	+1/-2	± 3	$\%f_{\text{intf_ft}}$	2
$f_{\text{intf_t}}$	Internal reference frequency (fast clock) — user trimmed at nominal V_{DD} and 25 °C	3	—	5	MHz	
$f_{\text{loc_low}}$	Loss of external clock minimum frequency — RANGE = 00	$(3/5) \times f_{\text{ints_t}}$	—	—	kHz	
$f_{\text{loc_high}}$	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	$(16/5) \times f_{\text{ints_t}}$	—	—	kHz	
FLL						
$f_{\text{fll_ref}}$	FLL reference frequency range		31.25	—	39.0625	kHz
f_{dco}	DCO output frequency range	Low range (DRS = 00)	20	20.97	25	MHz 3, 4
		$640 \times f_{\text{fll_ref}}$				
		Mid range (DRS = 01)	40	41.94	48	
		$1280 \times f_{\text{fll_ref}}$				

Table continues on the next page...

Table 12. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f _{dco_t_DMX32}	DCO output frequency	Low range (DRS = 00)	—	23.99	—	MHz	5, 6
		$732 \times f_{\text{fll_ref}}$					
		Mid range (DRS = 01)	—	47.97	—	MHz	
		$1464 \times f_{\text{fll_ref}}$					
J _{cyc_fll}	FLL period jitter f_{VCO} = 48 MHz		—	180	—	ps	7
t _{fll_acquire}	FLL target frequency acquisition time		—	—	1	ms	8
PLL							
f _{vco}	VCO operating frequency		48.0	—	100	MHz	
I _{pll}	PLL operating current PLL at 96 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	μA	9
I _{pll}	PLL operating current PLL at 48 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	μA	9
f _{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS) - f_{VCO} = 48 MHz - f_{VCO} = 100 MHz		— —	120 50	— —	ps ps	10
J _{acc_pll}	PLL accumulated jitter over 1μs (RMS) - f_{VCO} = 48 MHz - f_{VCO} = 100 MHz		— —	1350 600	— —	ps ps	10
D _{lock}	Lock entry frequency tolerance		± 1.49	—	± 2.98	%	
D _{uni}	Lock exit frequency tolerance		± 4.47	—	± 5.97	%	
t _{pll_lock}	Lock detector detection time		—	—	150 × 10 ⁻⁶ + 1075(1/f _{pll_ref})	s	11

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, $f_{\text{ints_ft}}$.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
4. The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation ($\Delta f_{\text{dco_t}}$) over voltage and temperature must be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification is based on standard deviation (RMS) of period or frequency.
8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
9. Excludes any oscillator currents that are also consuming power while PLL is in operation.
10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
11. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.

6.3.2.1 Oscillator DC electrical specifications

Table 13. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μA	
	• 8 MHz (RANGE=01)	—	300	—	μA	
	• 16 MHz	—	950	—	μA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	

Table continues on the next page...

Table 14. Oscillator frequency specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 15. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{hvp\text{pgm}4}$	Longword Program high-voltage time	—	7.5	18	μs	
$t_{h\text{versscr}}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{h\text{versall}}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands**Table 16. Flash command timing specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μ s	1
t_{pgmchk}	Program Check execution time	—	—	45	μ s	1
t_{rdsrc}	Read Resource execution time	—	—	30	μ s	1
t_{pgm4}	Program Longword execution time	—	65	145	μ s	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μ s	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μ s	
t_{ersall}	Erase All Blocks execution time	—	62	500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μ s	1

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors**Table 17. Flash high voltage current behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications**Table 18. NVM reliability specifications**

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$\eta_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 19](#) and [Table 20](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 19. 16-bit ADC operating conditions

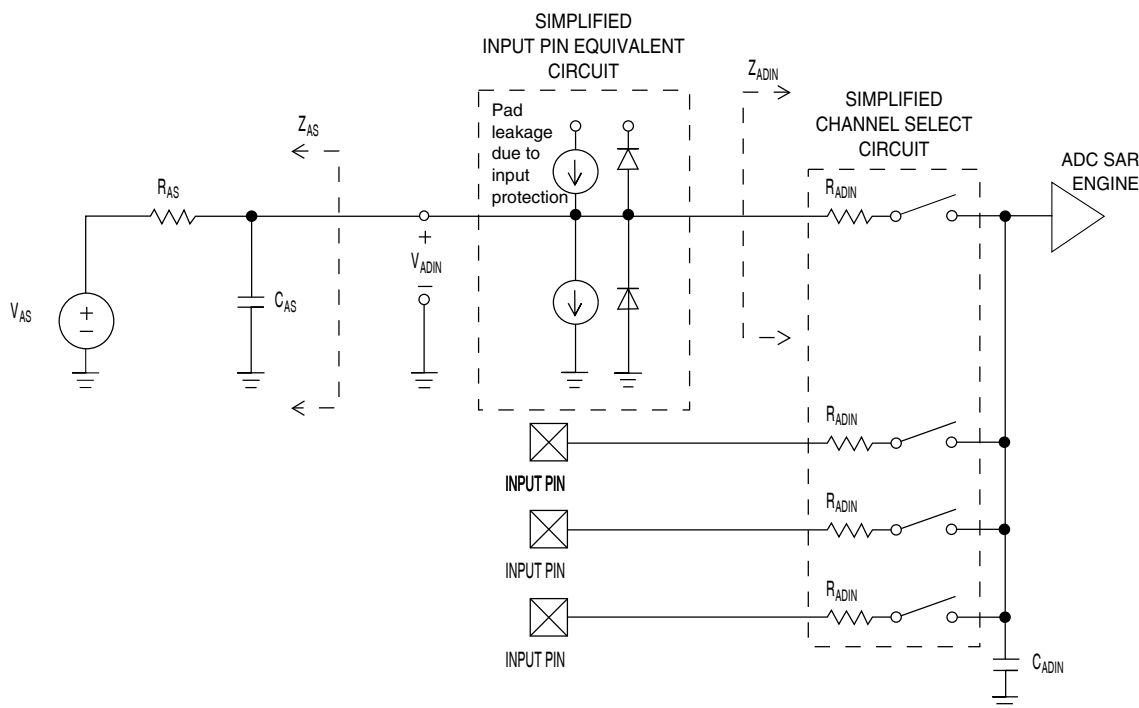
Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} -V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} - V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	3
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	3
V _{ADIN}	Input voltage		V _{REFL}	—	V _{REFH}	V	
C _{ADIN}	Input capacitance	16-bit mode 8-/10-/12-bit modes	— —	8 4	10 5	pF	
R _{ADIN}	Input resistance		—	2	5	kΩ	
R _{AS}	Analog source resistance	13-/12-bit modes f _{ADCK} < 4 MHz	—	—	5	kΩ	4
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	5
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	5
C _{rate}	ADC conversion rate	≤ 13 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

Table continues on the next page...

Table 19. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	6

1. Typical values assume $V_{DDA} = 3.0\text{ V}$, $\text{Temp} = 25\text{ }^{\circ}\text{C}$, $f_{ADCK} = 1.0\text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA} , and V_{REFL} is internally tied to V_{SSA} .
4. This resistance is external to MCU. The analog source resistance must be kept as low as possible to achieve the best results. The results in this data sheet were derived from a system which has $< 8\text{ }\Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to $< 1\text{ ns}$.
5. To use the maximum ADC conversion clock frequency, the ADHSC bit must be set and the ADLPC bit must be clear.
6. For guidelines and examples of conversion rate calculation, download the [ADC calculator tool](#)

**Figure 6. ADC input impedance equivalency diagram**

6.6.1.2 16-bit ADC electrical characteristics

Table 20. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3

Table continues on the next page...

Table 20. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	± 4 ± 1.4	± 6.8 ± 2.1	LSB ⁴	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	± 0.7 ± 0.2	-1.1 to +1.9 -0.3 to 0.5	LSB ⁴	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	± 1.0 ± 0.5	-2.7 to +1.9 -0.7 to +0.5	LSB ⁴	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB ⁴	$V_{ADIN} = V_{DDA}$ 5
E_Q	Quantization error	• 16-bit modes • ≤ 13-bit modes	— —	-1 to 0 —	— ± 0.5	LSB ⁴	
ENOB	Effective number of bits	16-bit differential mode • Avg = 32 • Avg = 4 16-bit single-ended mode • Avg = 32 • Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	$6.02 \times \text{ENOB} + 1.76$			dB	
THD	Total harmonic distortion	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	— —	-94 -85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	82 78	95 90	— —	dB dB	7

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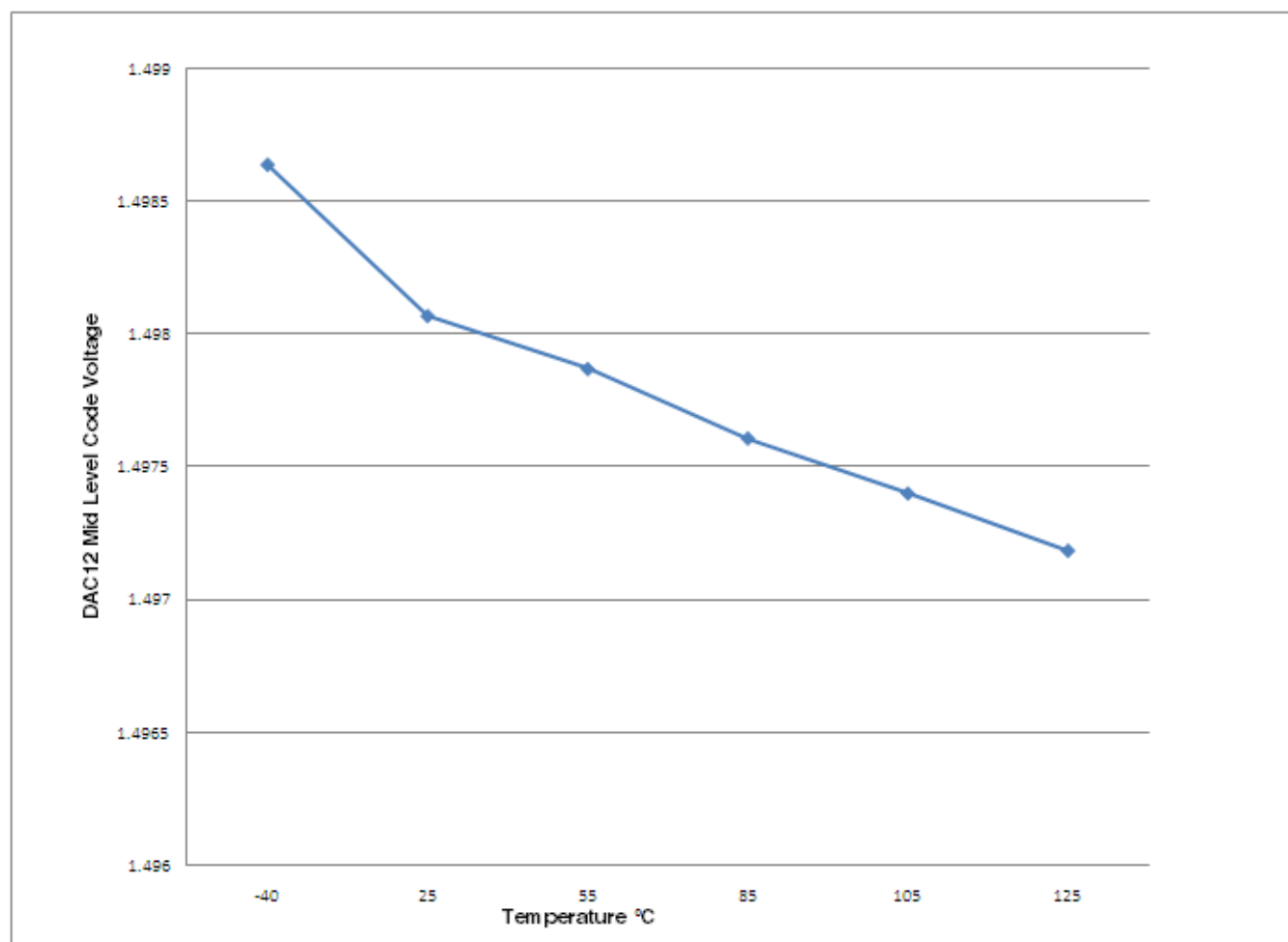


Figure 12. Offset at half scale vs. temperature

6.7 Timers

See General switching specifications.

6.8 Communication interfaces

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit <http://www.usb.org>.

6.8.2 USB VREG electrical specifications

Table 24. USB VREG electrical specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	—	120	186	μA	
I _{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	μA	
I _{DDoff}	Quiescent current — Shutdown mode - VREGIN = 5.0 V and temperature=25C - Across operating voltage and temperature	—	650	—	nA	
		—	—	4	μA	
I _{LOADrun}	Maximum load current — Run mode	—	—	120	mA	
I _{LOADstby}	Maximum load current — Standby mode	—	—	1	mA	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) > 3.6 V - Run mode - Standby mode	3	3.3	3.6	V	
		2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C _{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 25. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	f _{periph} /2048	f _{periph} /2	Hz	1

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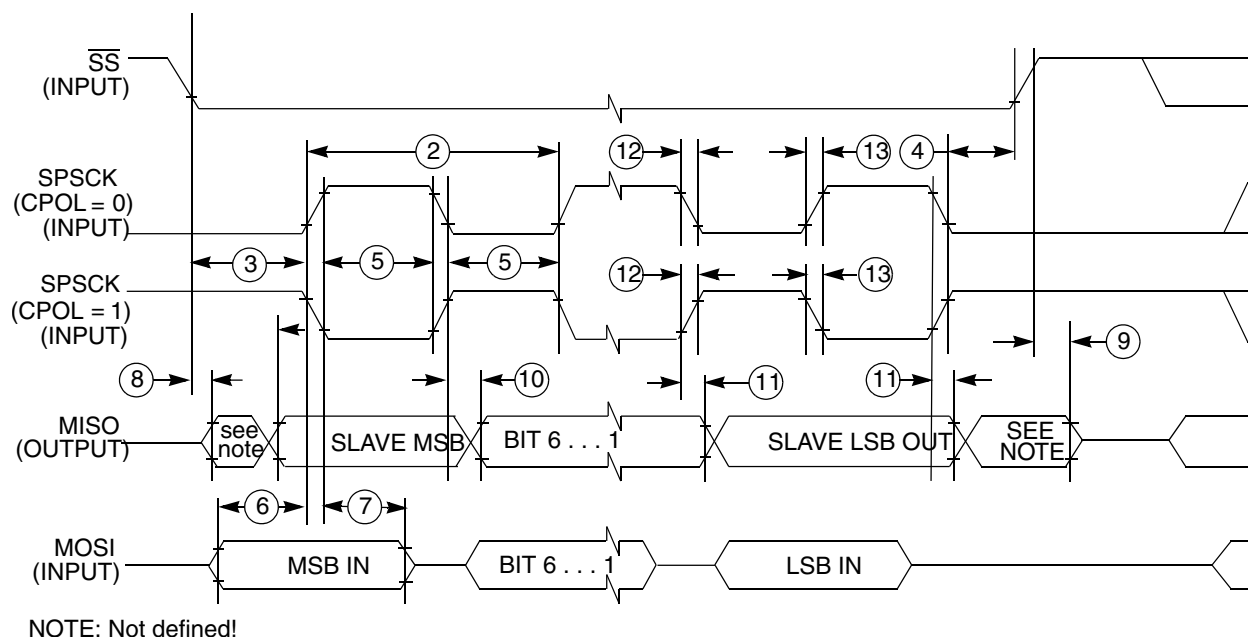


Figure 15. SPI slave mode timing (CPHA = 0)

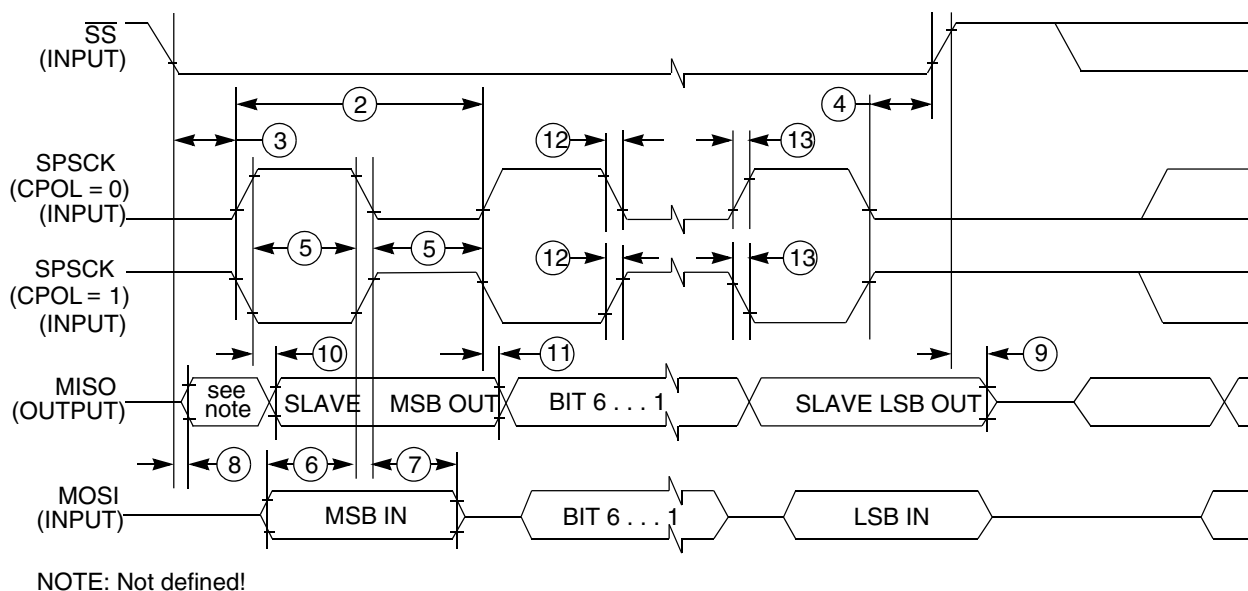


Figure 16. SPI slave mode timing (CPHA = 1)

6.8.4 I²C

See General switching specifications.

6.8.5 UART

See General switching specifications.

Pinout

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
64	52	40	28	PTC7	CMPO_IN1	CMPO_IN1	PTC7	SPI0_MISO			SPI0_MOSI		
65	53	—	—	PTC8	CMPO_IN2	CMPO_IN2	PTC8	I2C0_SCL	TPM0_CH4				
66	54	—	—	PTC9	CMPO_IN3	CMPO_IN3	PTC9	I2C0_SDA	TPM0_CH5				
67	55	—	—	PTC10	DISABLED		PTC10	I2C1_SCL					
68	56	—	—	PTC11	DISABLED		PTC11	I2C1_SDA					
69	—	—	—	PTC12	DISABLED		PTC12			TPM_CLKIN0			
70	—	—	—	PTC13	DISABLED		PTC13			TPM_CLKIN1			
71	—	—	—	PTC16	DISABLED		PTC16						
72	—	—	—	PTC17	DISABLED		PTC17						
73	57	41	—	PTD0	DISABLED		PTD0	SPI0_PCS0		TPM0_CH0			
74	58	42	—	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK		TPM0_CH1			
75	59	43	—	PTD2	DISABLED		PTD2	SPI0_MOSI	UART2_RX	TPM0_CH2	SPI0_MISO		
76	60	44	—	PTD3	DISABLED		PTD3	SPI0_MISO	UART2_TX	TPM0_CH3	SPI0_MOSI		
77	61	45	29	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI1_PCS0	UART2_RX	TPM0_CH4			
78	62	46	30	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI1_SCK	UART2_TX	TPM0_CH5			
79	63	47	31	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI1_MOSI	UART0_RX		SPI1_MISO		
80	64	48	32	PTD7	DISABLED		PTD7	SPI1_MISO	UART0_TX		SPI1_MOSI		

8.2 KL25 Pinouts

The below figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

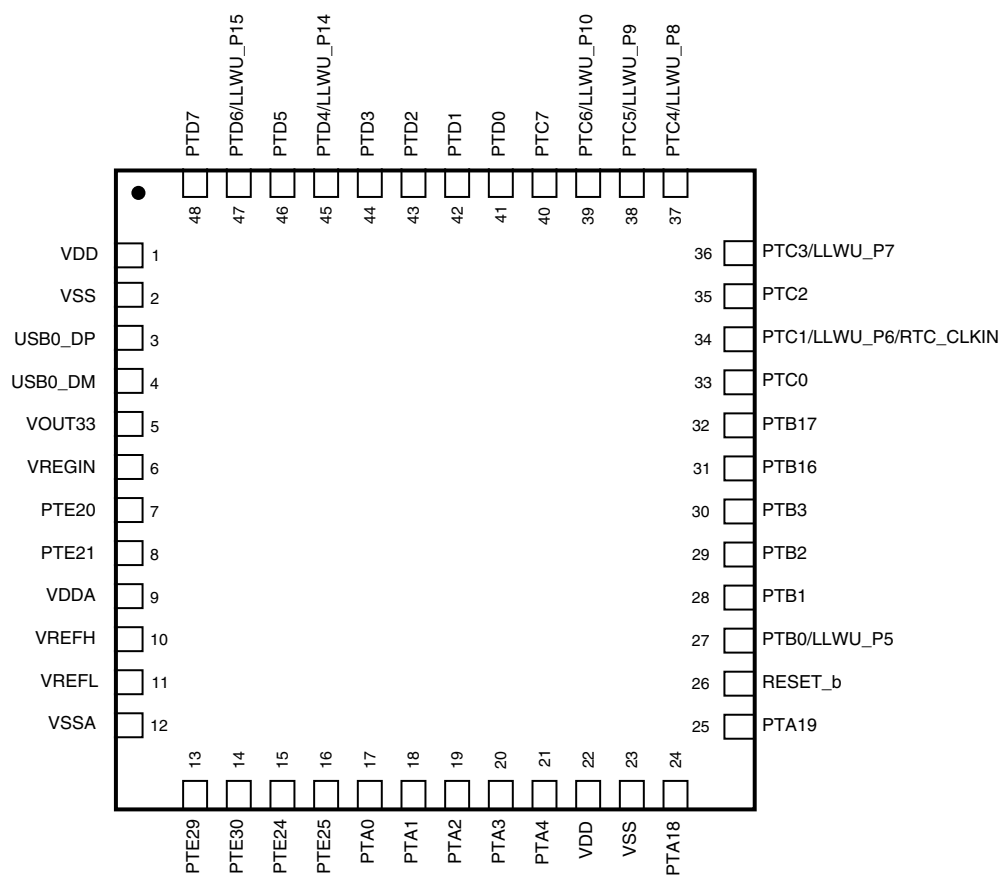


Figure 19. KL25 48-pin QFN pinout diagram